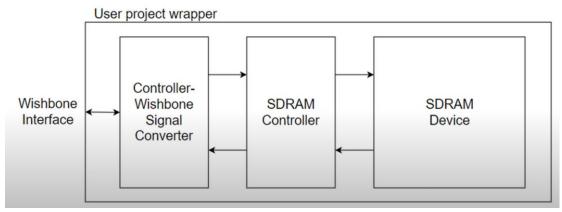
NYCU 電子研究所 系統晶片設計 LAB D

呂紹愷 311510187 江尹凡 311510207 廖智緯 311510216

Introduction

此次 Lab 與 4-1 十分相似,只是需要把 4-1 中的 BRAM 換成 SDRAM+SDRAM-controller,如下圖所示。



由於 SDRAM-controller 無法直接與 wishbone 做溝通, 因此中間需要再透過一個 converter 來做轉換。

SDRAM Device

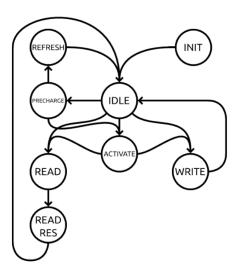
- o sdram_cle, sdram_cs, sdram_cas, sdram_ras, sdram_we
- sdram_dqm, sdram_ba, sdram_a
- sdram_dqi, sdram_dqo

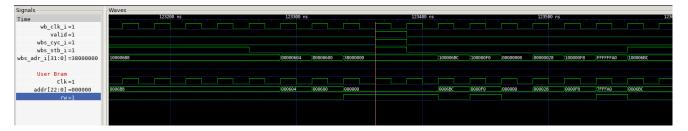
User interface

- user_addr
- o rw
- data_in, data_out
- busy
- o in valid, out valid

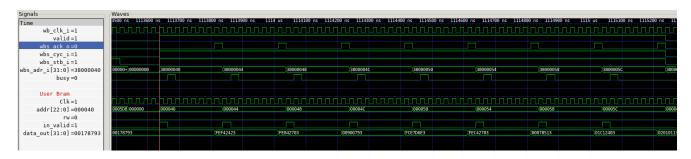
SDRAM Controller

- INIT→IDLE
- IDLE→ACTIVATE→WRITE→IDLE
- IDLE→ACTIVATE→READ→READ_RES
 →IDLE
- IDLE→WRITE→IDLE
- IDLE→READ→READ_RES→IDLE
- IDLE→PRECHARE→ACTIVATE→WRITE
 →IDLE
- IDLE→PRECHARE→ACTIVATE→READ
 →READ_RES→IDLE
- $IDLE \rightarrow PRECHARE \rightarrow REFRESH \rightarrow IDLE$





write



read (連續讀取) 經觀察可發現,本實驗中會連續讀取 8 筆 code 資訊,且地址為連續

• The behavior model refer to Micron MT48LC64M4A2

16 Meg x 4 x 4 banks

